SKiiP 13AC12T4V1



MiniSKiiP[®]1

3-phase bridge inverter

SKiiP 13AC12T4V1

Target Data

Features

- Trench 4 IGBT's
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

Typical Applications

Absolute Maximum Ratings $T_c = 25 \text{ °C}$, unless otherwise specified						
Symbol	_		Values			
IGBT						
V _{CES}	T _j = 25 °C		1200	V		
I _C	T _j = 175 °C	T _c = 25 °C	44	А		
		T _c = 70 °C	35	А		
I _{CRM}	I _{CRM} = 3xI _{Cnom}		75	А		
V _{GES}			±20	V		
t _{psc}	V_{CC} = 600 V; $V_{GE} \le 20$ V; VCES < 1200 V	T _j = 150 °C	10	μs		
Inverse D	Diode					
I _F	T _j = 175 °C	T _c = 25 °C	30	А		
		T _c = 70 °C	24	А		
I _{FRM}	I _{CRM} = 3xI _{Cnom}		75	А		
I _{FSM}	t _p = 10 ms; sin.	T _j = 150 °C	100	А		
Module				_		
I _{t(RMS)}			40	А		
T _{vj}			-40+175	°C		
T _{stg}			-40+125	°C		
V _{isol}	AC, 1 min.		2500	V		

Characteristics T _c =		25 °C, unless otherwise specified				
Symbol	Conditions		min.	typ.	max.	Units
IGBT	_					
V _{GE(th)}	$V_{GE} = V_{CE}, I_C = mA$		5	5,8	6,5	V
I _{CES}	$V_{GE} = V, V_{CE} = V_{CES}$	T _j = °C				mA
V _{CE0}		T _j = 25 °C		1,1	1,3	V
		T _j = 150 °C		1	1,2	V
r _{CE}	V _{GE} = 15 V	T _j = 25°C		30	30	mΩ
		T _j = 150°C		50	50	mΩ
V _{CE(sat)}	I _{Cnom} = 25 A, V _{GE} = 15 V			1,85	2,05	V
		T _j = 150°C _{chiplev.}		2,25	2,45	V
C _{ies}						nF
C _{oes}	V_{CE} = , V_{GE} = V	f = MHz				nF
C _{res}						nF
R _{Gint}	T _j = 25 °C			0		Ω
t _{d(on)}						ns
t,	R _{Gon} =	V _{CC} = 600V		•		ns
E _{on}	P -	I _{Cnom} = 25A T _i = 150 °C		3		mJ
t _{d(off)} t _f	R _{Goff} =	$V_{GE} = \pm 15V$				ns ns
ч Е _{off}		GE - C		2		mJ
R _{th(j-s)}	per IGBT	1		0,96		K/W

.K≯

. 🕻 🛧

AC

SKiiP 13AC12T4V1



MiniSKiiP[®]1

3-phase bridge inverter

SKiiP 13AC12T4V1

Target Data

Features

- Trench 4 IGBT's
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

Typical Applications

Characteristics							
Symbol	Conditions		min.	typ.	max.	Units	
Inverse D	ode						
$V_F = V_{EC}$	I_{Fnom} = 25 A; V_{GE} = 0 V	T _j = 25 °C _{chiplev.}		2,4	2,75	V	
		T _j = 150 °C _{chiplev.}		2,45	2,8	V	
V _{F0}		T _j = 25 °C		1,3	1,5	V	
		T _j = 150 °C		0,9	1,1	V	
r _F		T _j = 25 °C		44	50	mΩ	
		T _j = 150 °C		62	68	mΩ	
I _{RRM}	I _{Fnom} = A	T _j = 150 °C				А	
Q _{rr}		-				μC	
Err	$V_{GE} = \pm 15V$			1,88		mJ	
R _{th(j-s)}	per diode			1,7		K/W	
M _s	to heat sink		2		2,5	Nm	
w				35		g	
Tempera	ture sensor						
R _{ts}	3%, Tr=25°C			1000		Ω	
R _{ts}	3%, Tr=100°C			1670		Ω	

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.

AC

SKiiP 13AC12T4V1



